

Supporting Information

Efficient Quantum Dot Light-Emitting Diodes with $\text{Zn}_{0.85}\text{Mg}_{0.15}\text{O}$

Interfacial Modification Layer

Yizhe Sun¹, Yibin Jiang², Huiren Peng², Jiangliu Wei³, Shengdong Zhang^{1*}, Shuming Chen^{2*}

¹Institute of Microelectronics, Peking University, Beijing, P. R. China, 100871

zhangsd@pku.edu.cn

²Department of Electrical and Electronic Engineering, Southern University of Science and Technology, Shenzhen, P. R. China, 518055

chen.sm@sustc.edu.cn

³Guangdong Poly Optoelectronics Co., Ltd., Jiangmen, P. R. China, 529040

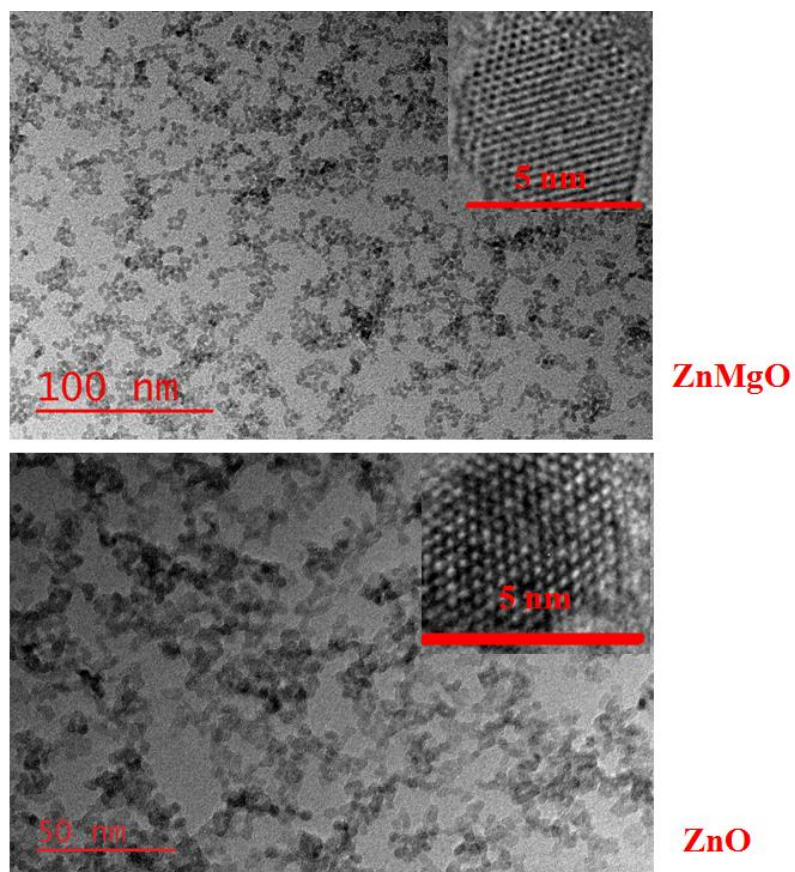


Figure S1. TEM images of the obtained ZnMgO and ZnO NPs.

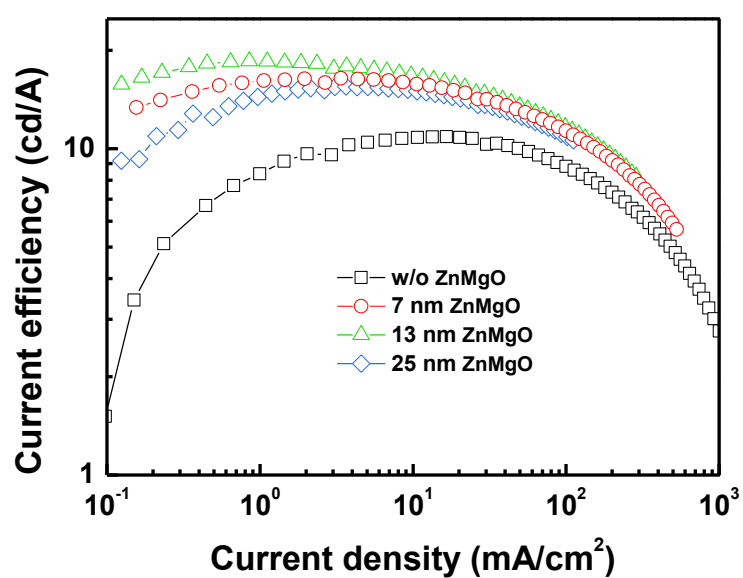


Figure S2. Current efficiency-J characteristics of the devices with different ZnMgO thickness.

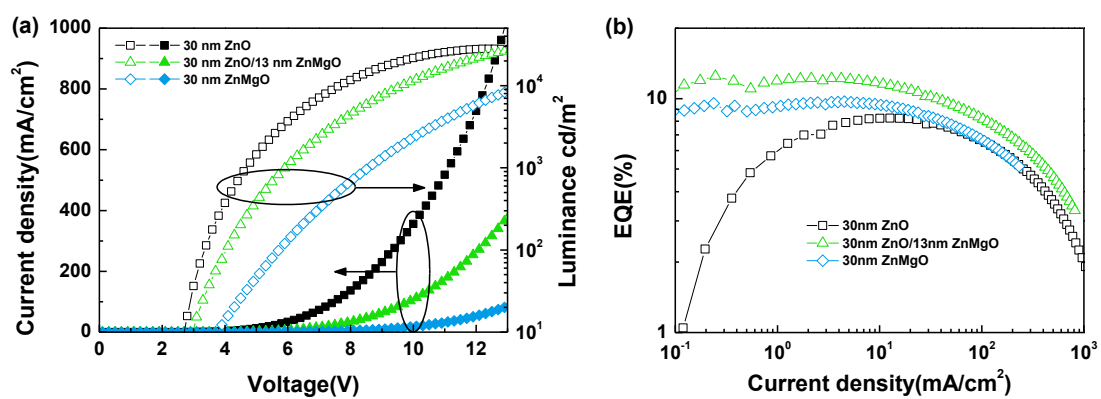


Figure S3. (a) J-V-L and (b) EQE-J characteristics of the inverted red QLEDs based on different ETL structures (ZnO, ZnO/ZnMgO, and ZnMgO).

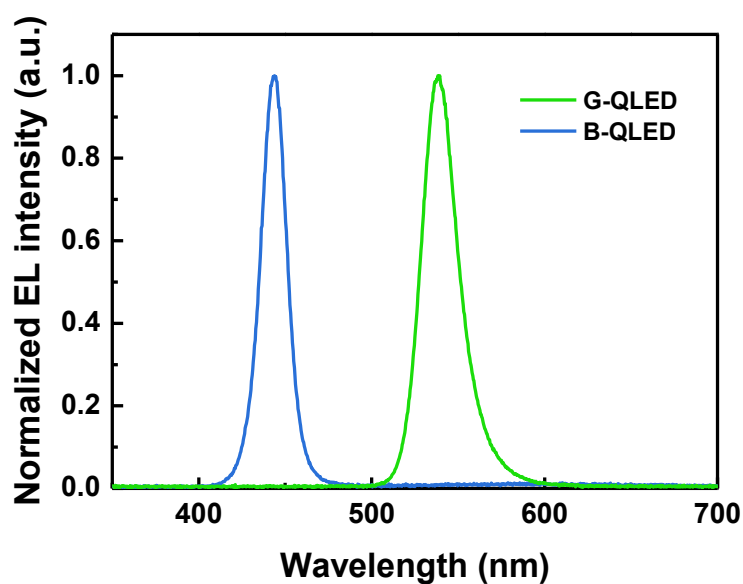


Figure S4. Normalized EL spectra of G-QLEDs and B-QLEDs.

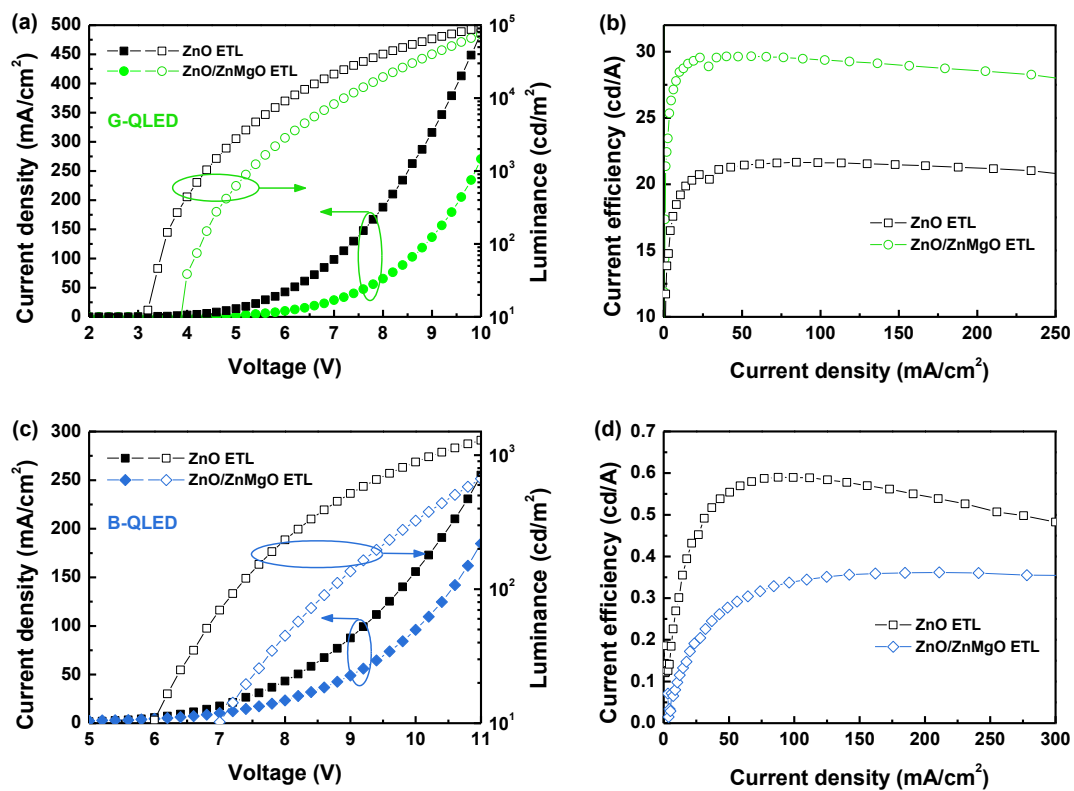


Figure S5. J-V-L and current efficiency-J characteristics of the inverted (a) (b) G-QLEDs and (c) (d) B-QLEDs.

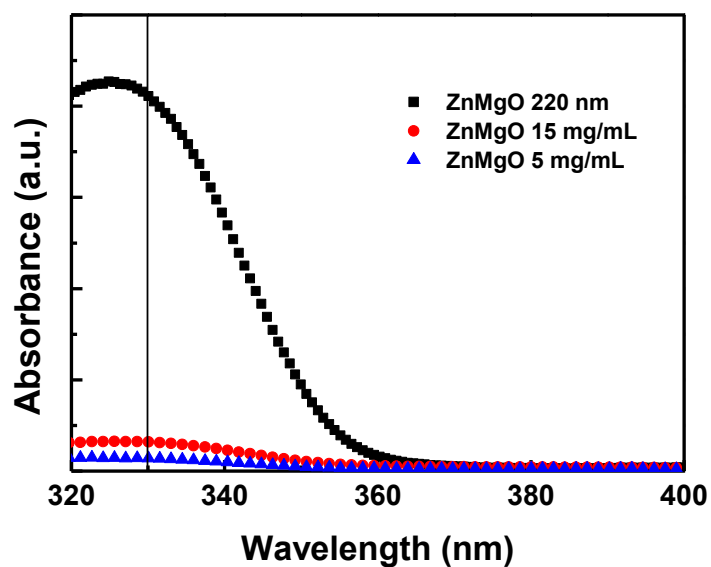


Figure S6. The absorbance of the ZnMgO films with different thicknesses.